

CMKT2907A  
CMKT2907AG

**SURFACE MOUNT  
DUAL PNP SILICON TRANSISTORS**

ULTRAm<sup>ini</sup><sup>™</sup>



**SOT-363 CASE**



www.centrasemi.com

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMKT2907A and CMKT2907AG each consist of two individual isolated 2907A PNP silicon transistors, manufactured by the epitaxial planar process and epoxy molded in an SOT-363 surface mount package. This ULTRAm<sup>ini</sup><sup>™</sup> device has been designed for small signal general purpose and switching applications.

- The CMKT2907AG is **Halogen Free** by design.

**MARKING CODES:**

CMKT2907A: K07

CMKT2907AG: K7G

**MAXIMUM RATINGS:** (T<sub>A</sub>=25°C)

Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	60	V
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	V
Continuous Collector Current	I <sub>C</sub>	600	mA
Power Dissipation	P <sub>D</sub>	350	mW
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
Thermal Resistance	θ <sub>JA</sub>	357	°C/W

**SYMBOL**

SYMBOL		UNITS
V <sub>CBO</sub>	60	V
V <sub>CEO</sub>	60	V
V <sub>EBO</sub>	5.0	V
I <sub>C</sub>	600	mA
P <sub>D</sub>	350	mW
T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
θ <sub>JA</sub>	357	°C/W

**ELECTRICAL CHARACTERISTICS PER TRANSISTOR:** (T<sub>A</sub>=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I <sub>CBO</sub>	V <sub>CB</sub> =50V		10	nA
I <sub>CBO</sub>	V <sub>CB</sub> =50V, T <sub>A</sub> =125°C		10	μA
I <sub>CEV</sub>	V <sub>CE</sub> =30V, V <sub>BE</sub> =0.5V		50	nA
BV <sub>CBO</sub>	I <sub>C</sub> =10μA	60		V
BV <sub>CEO</sub>	I <sub>C</sub> =10mA	60		V
BV <sub>EBO</sub>	I <sub>E</sub> =10μA	5.0		V
V <sub>CE(SAT)</sub>	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA		0.4	V
V <sub>CE(SAT)</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA		1.6	V
V <sub>BE(SAT)</sub>	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA		1.3	V
V <sub>BE(SAT)</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA		2.6	V
h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =0.1mA	75		
h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =1.0mA	100		
h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA	100		
h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =150mA	100	300	
h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =500mA	50		

R4 (13-January 2010)

**CMKT2907A  
CMKT2907AG**

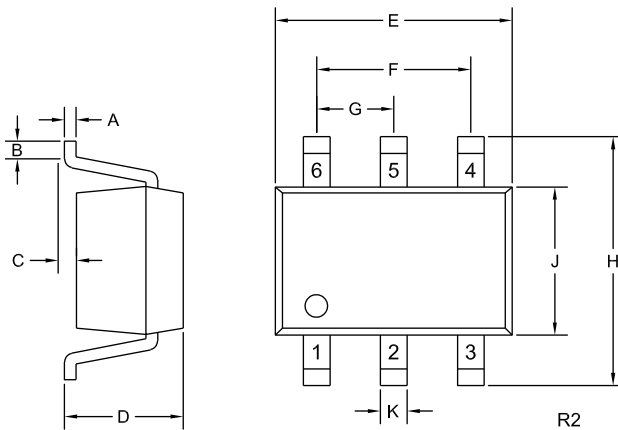
**SURFACE MOUNT  
DUAL PNP SILICON TRANSISTORS**



**ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued:**

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$f_T$	$V_{CE}=20V, I_C=50mA, f=100MHz$	200		MHz
$C_{ob}$	$V_{CB}=10V, I_E=0, f=1.0MHz$		8.0	pF
$C_{ib}$	$V_{BE}=2.0V, I_C=0, f=1.0MHz$		30	pF
$t_{on}$	$V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA$		45	ns
$t_d$	$V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA$		10	ns
$t_r$	$V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA$		40	ns
$t_{off}$	$V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA$		100	ns
$t_s$	$V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA$		80	ns
$t_f$	$V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA$		30	ns

**SOT-363 CASE - MECHANICAL OUTLINE**



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.010	0.10	0.25
B	0.005	-	0.12	-
C	0.000	0.004	0.00	0.10
D	0.031	0.043	0.80	1.10
E	0.071	0.087	1.80	2.20
F	0.051		1.30	
G	0.026		0.65	
H	0.075	0.091	1.90	2.30
J	0.043	0.055	1.10	1.40
K	0.006	0.012	0.15	0.30

SOT-363 (REV: R2)

**LEAD CODE:**

- 1) Emitter Q1
- 2) Base Q1
- 3) Collector Q2
- 4) Emitter Q2
- 5) Base Q2
- 6) Collector Q1

**MARKING CODES:**

**CMKT2907A: K07**  
**CMKT2907AG: K7G**

R4 (13-January 2010)